

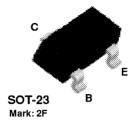
Discrete POWER & Signal Technologies

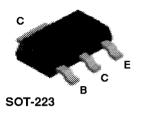
PN2907A

MMBT2907A

PZT2907A

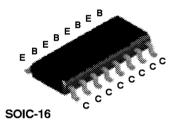


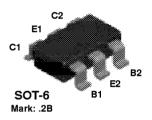




MMPQ2907

NMT2907





PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _B	Base Cutoff Current	$V_{CB} = 30 \text{ V}, V_{EB} = 0.5 \text{ V}$		50	nA
I _{CEX}	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{BE} = 0.5 \text{ V}$		50	nA
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_{E} = 0$		0.02	μΑ
		$V_{CB} = 50 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		20	μA
			1 100	1	
h _{FF}	ACTERISTICS T DC Current Gain	$I_{C} = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$	75		T
		$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	100		
		$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^*$	100 100	300	
		$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}^*$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}^*$	100		
V _{CE(sat)}	Collector-Emitter Saturation Voltage*	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 150 \text{ mA}, \ I_{B} = 15 \text{ mA} \end{split}$	100 100	0.4	V
		$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 150 \text{ mA}, \ I_{B} = 15 \text{ mA} \\ I_{C} &= 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \end{split}$	100 100	0.4 1.6	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage* Base-Emitter Saturation Voltage	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 550 \text{ mA}, \ I_{B} = 15 \text{ mA} \\ I_{C} &= 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \\ I_{C} &= 150 \text{ mA}, \ I_{B} = 15 \text{ mA}^{*} \end{split}$	100 100	0.4	
		$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA}, \ V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 150 \text{ mA}, \ I_{B} = 15 \text{ mA} \\ I_{C} &= 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \end{split}$	100 100	0.4 1.6 1.3	V
V _{BE(sat)}		$\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_C &= 150 \text{ mA, } V_{CE} = 10 \text{ V}^* \\ I_C &= 500 \text{ mA, } V_{CE} = 10 \text{ V}^* \\ I_C &= 150 \text{ mA, } I_B = 15 \text{ mA} \\ I_C &= 500 \text{ mA, } I_B = 50 \text{ mA} \\ I_C &= 150 \text{ mA, } I_B = 15 \text{ mA}^* \\ I_C &= 500 \text{ mA, } I_B = 50 \text{ mA} \end{split}$	100 100	0.4 1.6 1.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$\begin{split} I_{C} &= 10 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_{C} &= 150 \text{ mA, } V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA, } V_{CE} = 10 \text{ V}^{*} \\ I_{C} &= 500 \text{ mA, } I_{B} = 15 \text{ mA} \\ I_{C} &= 500 \text{ mA, } I_{B} = 50 \text{ mA} \\ I_{C} &= 150 \text{ mA, } I_{B} = 15 \text{ mA}^{*} \\ I_{C} &= 500 \text{ mA, } I_{B} = 50 \text{ mA} \\ \end{split}$	100 100	0.4 1.6 1.3	V
V _{BE(Sat)}	Base-Emitter Saturation Voltage GNAL CHARACTERISTICS (exce	$\begin{split} I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V} \\ I_C &= 150 \text{ mA, } V_{CE} = 10 \text{ V}^* \\ I_C &= 500 \text{ mA, } V_{CE} = 10 \text{ V}^* \\ I_C &= 500 \text{ mA, } I_B = 15 \text{ mA} \\ I_C &= 500 \text{ mA, } I_B = 50 \text{ mA} \\ I_C &= 150 \text{ mA, } I_B = 15 \text{ mA}^* \\ I_C &= 500 \text{ mA, } I_B = 50 \text{ mA} \\ \end{split}$	100 100 50	0.4 1.6 1.3	V V V

SWITCHING CHARACTERISTICS (except MMPQ2907 and NMT2907)

t _{on}	Turn-on Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$	45	ns
t _d	Delay Time	I _{B1} = 15 mA	10	ns
t _r	Rise Time		40	ns
t _{off}	Turn-off Time	$V_{CC} = 6.0 \text{ V}, I_{C} = 150 \text{ mA}$	100	ns
t _s	Storage Time	$I_{B1} = I_{B2} = 15 \text{ mA}$	80	ns
t _f	Fall Time		30	ns

^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

Spice Model

 $PNP (Is=650.6E-18 \ Xti=3 \ Eg=1.11 \ Vaf=115.7 \ Bf=231.7 \ Ne=1.829 \ Ise=54.81f \ Ikf=1.079 \ Xtb=1.5 \ Br=3.563 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=.715 \ Cjc=14.76p \ Mjc=.5383 \ Vjc=.75 \ Fc=.5 \ Cje=19.82p \ Mje=.3357 \ Vje=.75 \ Tr=111.3n \ Tf=603.7p \ Itf=.65 \ Vtf=5 \ Xtf=1.7 \ Rb=10)$

(continued)

Thermal Characteristics TA = 25°C

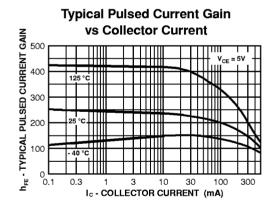
TA = 25°C unless otherwise noted

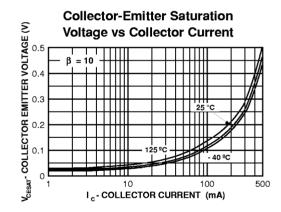
Symbol	Characteristic	Max		Units
		PN2907A	*PZT2907A	
P _D	Total Device Dissipation	625	1,000	mW
	Derate above 25°C	5.0	8.0	mW/°C
R _{euc}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{eua}	Thermal Resistance, Junction to Ambient	200	125	°C/W

Symbol	Characteristic	Max		Units
		**MMBT2907A	MMPQ2907	
P_{D}	Total Device Dissipation Derate above 25°C	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	357	125 240	°C/W °C/W °C/W

^{*}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

Typical Characteristics

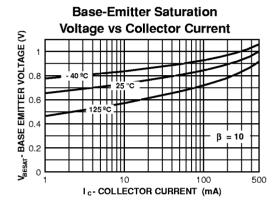


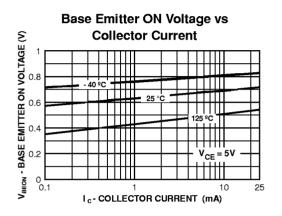


^{**}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

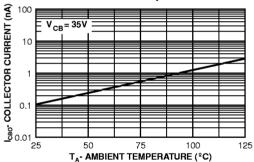
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Typical Characteristics (continued)

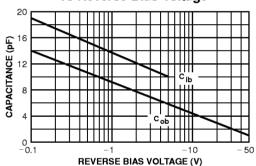




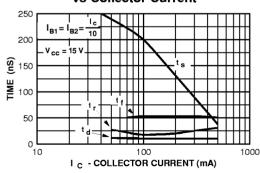
Collector-Cutoff Current vs. Ambient Temperature



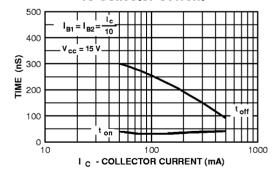
Input and Output Capacitance vs Reverse Bias Voltage



Switching Times vs Collector Current

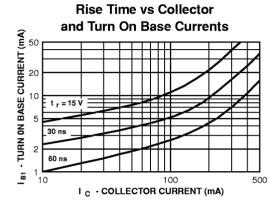


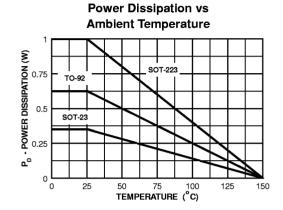
Turn On and Turn Off Times vs Collector Current



(continued)

Typical Characteristics (continued)





Test Circuits

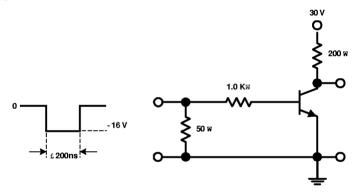


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

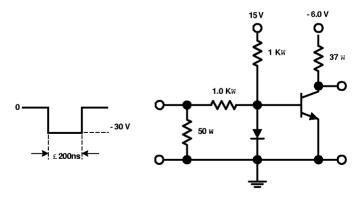


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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